

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

2SA1213-x-MS

Product specification

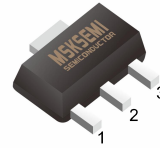
TRANSISTOR (PNP)

FEATURE

- Complementary to 2SC2873-x-MS
- Small Flat Package
- Power Amplifier and Switching Applications
- Low Saturation Voltage
- High Speed Switching Time

Reference News

SOT-89



1. BASE
2. COLLECTOR
3. EMITTER

MARKING

2SA1213-O-MS	2SA1213-Y-MS
	

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-2	A
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

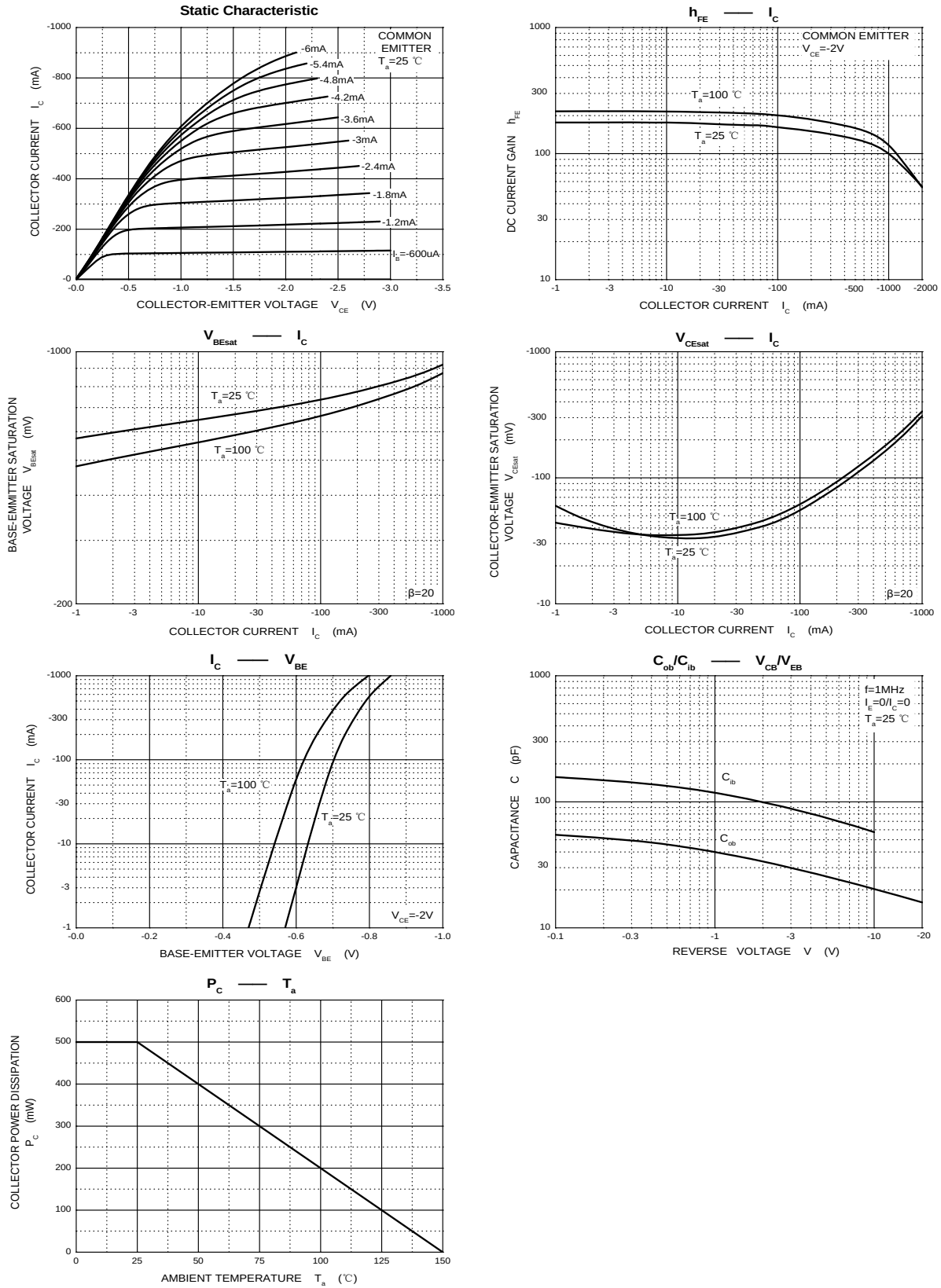
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1\text{mA}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-100	nA
DC current gain	h_{FE}	$V_{CE} = -2\text{V}, I_C = -500\text{mA}$	70		240	
		$V_{CE} = -2\text{V}, I_C = -2\text{A}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1\text{A}, I_B = -50\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -1\text{A}, I_B = -50\text{mA}$			-1.2	V
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		40		pF
Transition frequency	f_T	$V_{CE} = -2\text{V}, I_C = -0.5\text{A}$	100			MHz

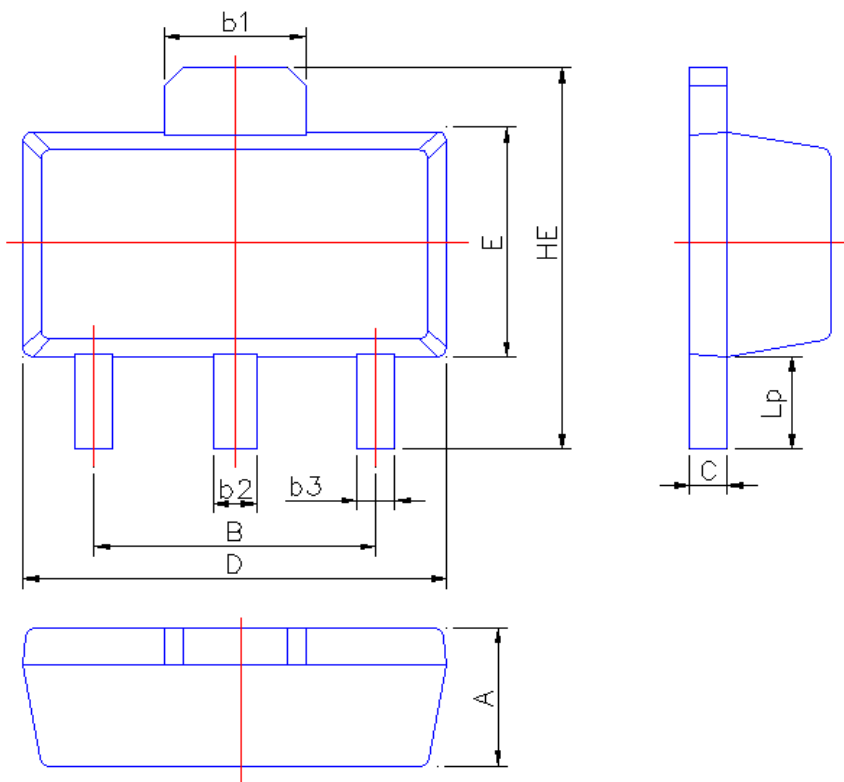
CLASSIFICATION OF h_{FE}

Rank	2SA1213-O-MS	2SA1213-Y-MS
Range	70 -140	120-240

Typical Characteristics



PACKAGE MECHANICAL DATA



SOT-89

Symbol	Dimension in Millimeters	
	Min	Max
A	1.40	1.60
B	2.95	3.05
b1	1.45	1.70
b2	0.45	0.60
b3	0.35	0.50
C	0.35	0.50
D	4.40	4.60
E	2.35	2.55
HE	3.90	4.40
Lp	0.90	1.10

REELS SPECIFICATION

P/N	PKG	QTY
2SA1213-x-MS	SOT-89	1000

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